

MicroPatent® PatSearch Fulltext: Record 1 of 1

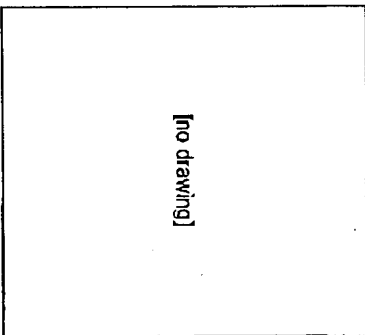
Search scope: US Granted US Applications EP-A-EP-8 WO JP (bibliographic data only) DE-C,B DE-A DE-I DE-U GB-A FR-A
Years: 1981-2006
Patent/Publication No.: ((JP2004133384))

Order/Download Family Lookup Find Similar Legal Status
Go to first matching text

JP2004133384 A
RESIST REMOVING AGENT
COMPOSITION AND METHOD FOR
MANUFACTURING
SEMICONDUCTOR DEVICE
SONY CORP EKC TECHNOLOGY KK

Abstract:

PROBLEM TO BE SOLVED: To provide a resist removing agent composition having such components that photoresist residues or polymers after dry etching are easily removed and an insulating film with a low dielectric constant is not corroded or oxidized.SOLUTION: One



example of the resist removing agent composition comprises: 5.0 wt. % of sulfamic acid, 34.7 wt. % of H₂O, 0.3 wt. % of ammonium hydrogendifluoride, 30 wt. % of N, N dimethyl acetamide; and 30 wt. % of ethyleneglycol mono n-butylether. Another example of the resist removing agent composition comprises: 3.0 wt. % of 1-hydroxyethylidene-1,1-diphosphonic acid, 0.12 wt. % of ammonium fluoride, 48.4 wt. % of H₂O, and 48.5 wt. % of diethyleneglycol mono n-butylether. The resist removing agent composition is primarily used as a chemical cleaning liquid to remove the resist residue and byproduct polymers after the ashing process of a resist mask.

Inventor(s):

MURAMATSU MASAFUMI
IWAMOTO ISATO
ASADA KAZUMI
SUZUKI TOMOKO
HIRAGA TOSHITAKA
AOYAMA TETSUO

Application No. 2003159192 JP2003159192 JP, Filed 20030604, A1
Published 20040430

Original IPC(1-7): G03F00742
H01L021027 H01L021304 H01L021788

Priority:
JP 2002236559 20020814

Patents Citing This One No US, EP, or WO patent/search reports have cited this patent.

For further information, please contact:
Technical Support | Billing | Sales | General Information